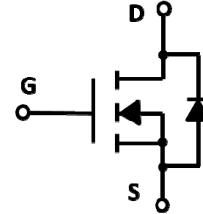


N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} 60V
- I_D 20A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <43mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) <47 mohm
- 100% UIS Tested
- 100% ∇V_{DS} Tested

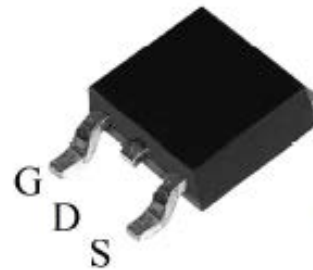


General Description

- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

- DC-DC Converters
- Power management functions
- Backlighting



TO-252

■ Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	60	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_C=25^{\circ}C$	I_D	20	A
	$T_C=100^{\circ}C$		14	
Pulsed Drain Current ^A		I_{DM}	60	A
Total Power Dissipation	$T_C=25^{\circ}C$	P_D	34	W
	$T_C=100^{\circ}C$		17	
Single Pulse Avalanche Energy ^B		E_{AS}	20	mJ
Thermal Resistance Junction-to-Case ^C		$R_{\theta JC}$	4.4	$^{\circ}C/W$
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+175	$^{\circ}C$

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	$T_J=25^\circ\text{C}$		1	μA
			$T_J=55^\circ\text{C}$		5	
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		34	43	m Ω
		$V_{GS}=4.5V, I_D=10A$		36	47	
Diode Forward Voltage	V_{SD}	$I_S=10A, V_{GS}=0V$		0.8	1.2	V
Maximum Body-Diode Continuous Current	I_S				20	A
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V, f=1\text{MHz}$		800		pF
Output Capacitance	C_{oss}			68		
Reverse Transfer Capacitance	C_{rss}			36		
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=30V, I_D=10A$		15		nC
Gate-Source Charge	Q_{gs}			2.4		
Gate-Drain Charge	Q_{gd}			2.5		
Reverse Recovery Charge	Q_{rr}	$I_F=20A, di/dt=500A/\mu s$		23		ns
Reverse Recovery Time	t_{rr}			45		
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=30V, I_D=2A, R_L=1\Omega$ $R_{GEN}=3\Omega$		5		ns
Turn-on Rise Time	t_r			39		
Turn-off Delay Time	$t_{D(off)}$			19		
Turn-off fall Time	t_f			7		

Typical Performance Characteristics

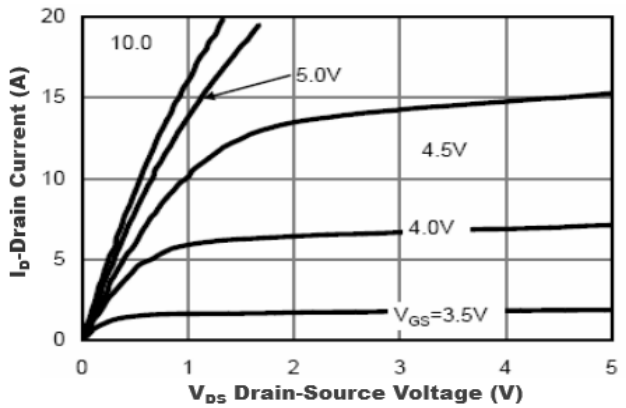


Figure1. Output Characteristics

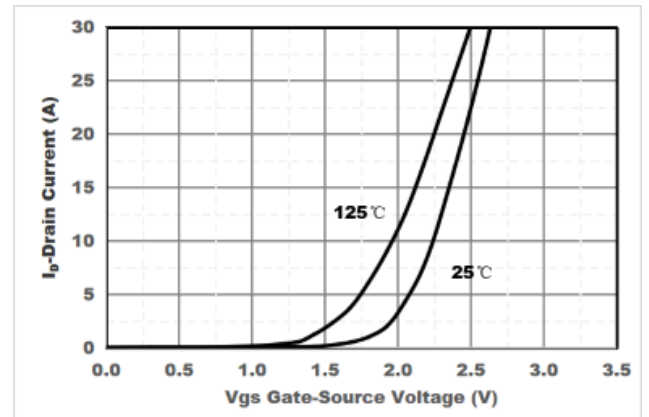


Figure2. Transfer Characteristics

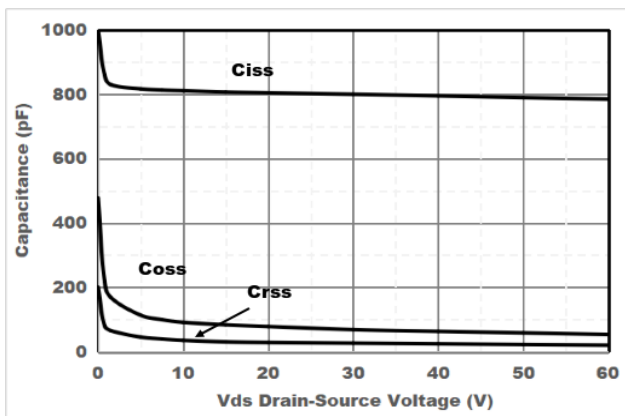


Figure3. Capacitance Characteristics

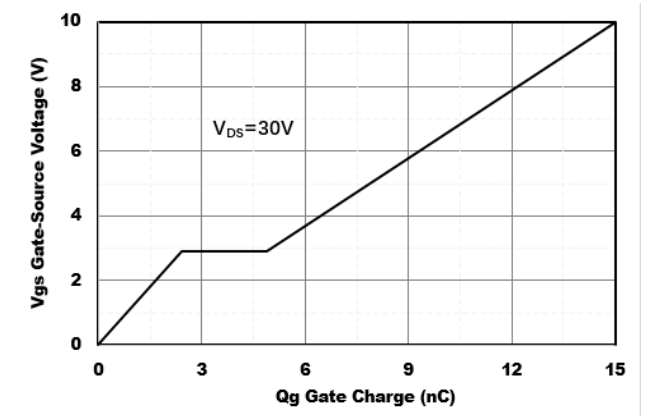


Figure4. Gate Charge

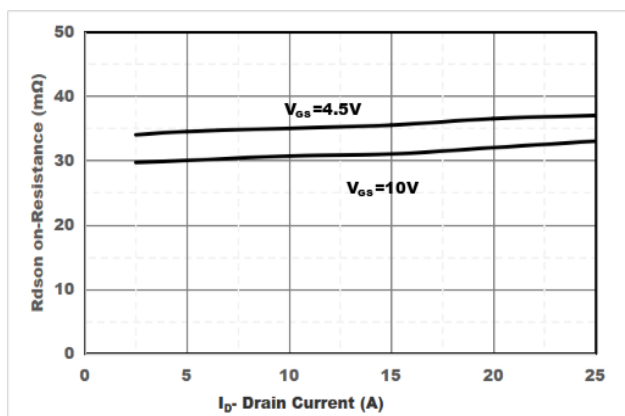


Figure5. Drain-Source on Resistance

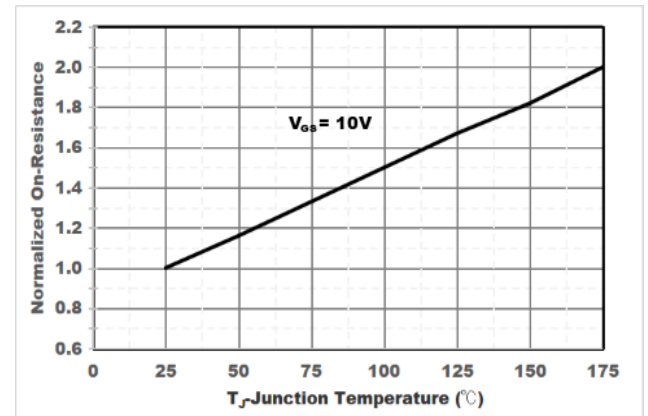


Figure6. Drain-Source on Resistance

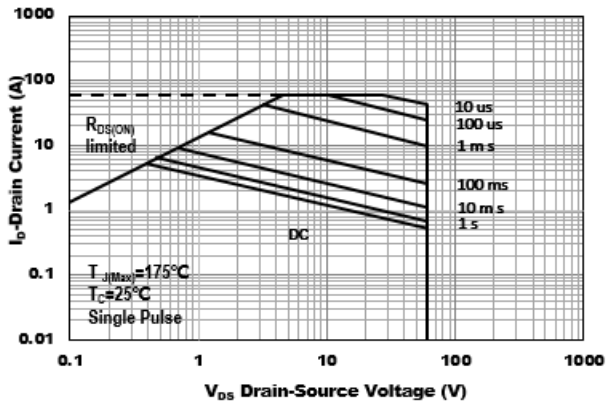


Figure7. Safe Operation Area

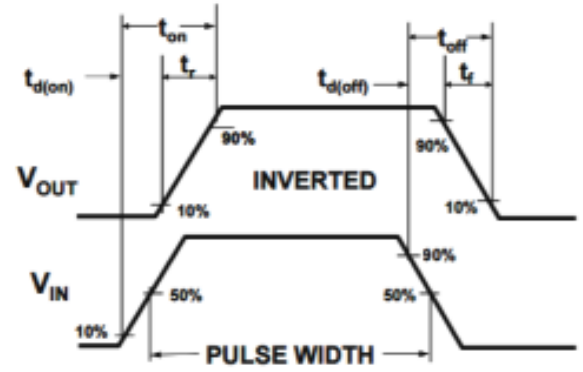
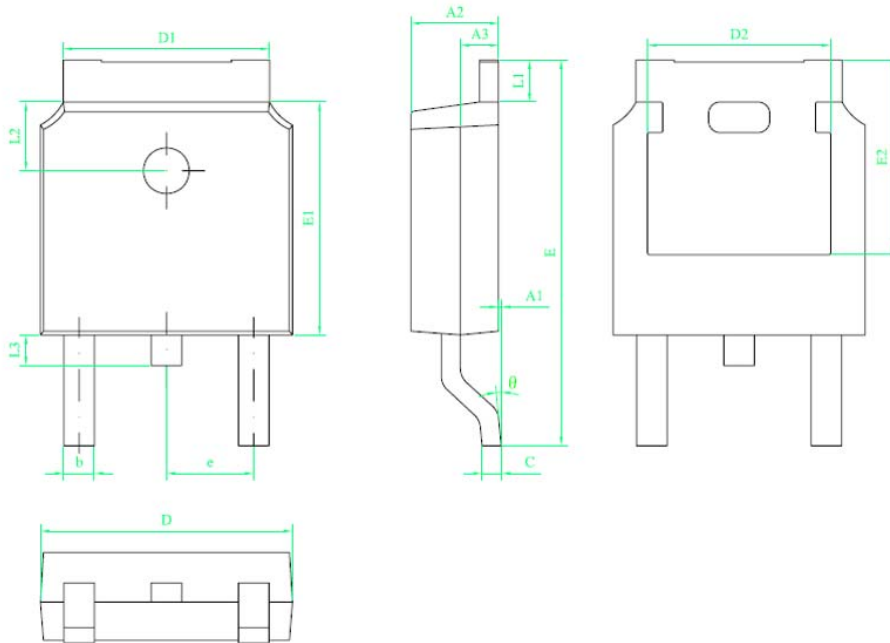


Figure8. Switching wave

■ TO-252 Package Information



Symbol	(mm)		
	min	nom	max
A1	0	----	0.10
A2	2.20	2.30	2.40
A3	0.90	1.00	1.10
b	0.75	----	0.85
c	0.50	----	0.60
D	6.50	6.60	6.70
D1	5.30	5.40	5.50
D2	4.70	4.80	4.90
E	9.90	10.10	10.30
E1	6.00	6.10	6.20
E2	5.20	5.30	5.40
e	2.20	2.286	2.40
L1	0.90	----	1.25
L2	1.70	1.80	1.90
L3	0.60	0.80	1.00
θ	0°	----	8°

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)